

AgGaGeS₄



DESCRIPTION

AgGaGeS₄ (Silver Germanium Gallium Sulfide) is a negative biaxial crystal with an orthogonal crystal system and a larger nonlinear coefficient than AgGaS. Compared with conventional materials, AgGaGeS₄ has a wide transmission band (0.5~11.5 μm), a small absorption coefficient ($\alpha < 0.005 \text{ cm}^{-1}$), and a high threshold of laser damage resistance (30 ns, 9.55 μm, 230 MW/cm²), which is about 1.6 times that of AgGaS₂ (149 MW/cm²), ZnGeP₂ (142 MW/cm²) 1.6 times, suitable for titanium gem 800 nm, Nd:YAG 1 μm laser pumping birefringence (0.057); can be applied to CO₂ laser frequency doubling, can withstand high-power laser pumping, output high power mid and far infrared laser.

FEATURES

- High output power
- Low absorption coefficient
- High laser damage threshold
- Withstand high power laser pumping
- High nonlinear optical coefficient wide transmission range

APPLICATIONS

- Optical parametric oscillation
- Optical parametric amplification

PROCESSING PARAMETERS

Orientation accuracy	<+/- 0.1°
Surface finish	20/10 per MIL-O-13830A
Face Type	$\lambda/8@632.8\text{nm}$ When $T \geq 1\text{mm}$
Through surface tolerance	+0/-0.1mm
Length Tolerance	±0.1mm
Parallelism	30 "
Perpendicularity	10'
reverse side	<0.2mm×45°



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PHYSICAL AND CHEMICAL PROPERTIES

Nonlinear optical coefficients	$d_{31}=15 \text{ pm/V}$
Transmittance range	0.5-11.5 μm
Absorption coefficient	0.05 cm^{-1} @1064 nm
Damage Threshold	$>1.2\text{J/cm}^2$ @1064nm
Crystal Structure	Orthogonal crystal system, Fdd2 space group
Cell parameters	$a=12.015\text{\AA}, b=22.904\text{\AA}, c=6.874\text{\AA}$
Melting point	850 $^{\circ}\text{C}$
Band Gap	2.78eV
Transmittance range	0.5-11.5 μm
Birefringence	0.0751@0.5 μm
	0.0656@0.6 μm
	0.0582@0.8 μm
	0.0555@1.064 μm
	0.0545@2 μm
	0.0516@4 μm
	0.0333@10.6 μm
	0.0301@11.5 μm

SPECTRA

